Hex 3-State Noninverting Buffer with Separate 2-Bit and 4-Bit Sections

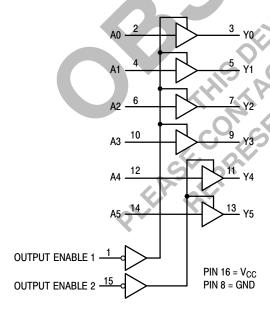
High-Performance Silicon-Gate CMOS

The MC74HC367A is identical in pinout to the LS367. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device is arranged into 2-bit and 4-bit sections, each having its own active-low Output Enable. When either of the enables is high, the affected buffer outputs are placed into high-impedance states. The HC367A has noninverting outputs.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 92 FETs or 23 Equivalent Gates

LOGIC DIAGRAM





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N SUFFIX PLASTIC PACKAGE

16-LEAD CASE 648-08



D SUFFIX

SOIC PACKAGE 16-LEAD CASE 751B-05



DT SUFFIX

TSSOP PACKAGE 16-LEAD CASE 948F-01

ORDERING INFORMATION

MC74HCXXXAN Plastic MC74HCXXXAD SOIC MC74HCXXXADT TSSOP

PIN ASSIGNMENT

OUTPUT ENABLE 1	1 •	16	v _{cc}
ENABLE 1 4	1 •	10	
A0 [2	15	OUTPUT ENABLE 2
Y0 [3	14] A5
A1 [4	13	Y5
Y1 [5	12	A4
A2 [6	11	Y4
Y2 [7	10	A3
GND [8	9	Y3

FUNCTION TABLE

Inpu	Output	
Enable 1, Enable 2	Α	Υ
L	L	L
L	Н	Н
Н	Х	Z

X = don't care Z = high impedance

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	±[2 0	mA
I _{out}	DC Output Current, per Pin	±[2 5	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±[5 0	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

For high fre	TSSOP Package: – 6.1 mW/°C from 6 quency or heavy load considerations, se	5° to 125°C	ne Motor	ola High	-Speed	d CMOS Data Book (DL12
RECOMM	ENDED OPERATING CONDITIONS		\mathbf{X}			IN WINDS
Symbol	Parameter		Min	Max	Unit	(C, D)
V _{CC}	DC Supply Voltage (Referenced to GND))	2.0	6.0	V	
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V_{CC}	V	.01
T _A	Operating Temperature, All Package Ty	oes	- 55	+ 125	°C	
t _r , t _f	Input Rise and Fall Time (Figure 1)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 3.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0 0	1000 600 500 400	ns	

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC} V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$\begin{aligned} V_{out} &= V_{CC} - 0.1 \text{ V} \\ I_{out} &\leq 20 \mu\text{A} \end{aligned}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\begin{aligned} V_{in} = V_{IH} & & I_{out} \leq 3.6 \text{ mA} \\ & I_{out} \leq 6.0 \text{ mA} \\ & I_{out} \leq 7.8 \text{ mA} \end{aligned}$	4.5	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	

^{*}Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

Plastic DIP: - 10 mW/°C from 65° to 125°C SOIC Package: - 7 mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC} V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\label{eq:Vin} \begin{array}{ll} V_{in} = V_{IL} & I_{out} \leq 3.6 \text{ mA} \\ I_{out} \leq 6.0 \text{ mA} \\ I_{out} \leq 7.8 \text{ mA} \end{array}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±[0.1	± <u>∏</u> 1.0	±[1.0	μΑ
I _{OZ}	Maximum Three–State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	6.0	±[0.5	±[ō.0	± <u>1</u> 10	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

			Guaranteed Limit			
Symbol	Parameter	V _{CC} V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	2.0 3.0 4.5 6.0	120 60 24 20	150 75 30 26	180 90 36 31	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	175 90 35 30	220 110 44 37	265 135 53 45	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	190 95 38 32	240 120 48 21	285 150 57 48	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C _{in}	Maximum Input Capacitance	_	10	10	10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	_	15	15	15	pF

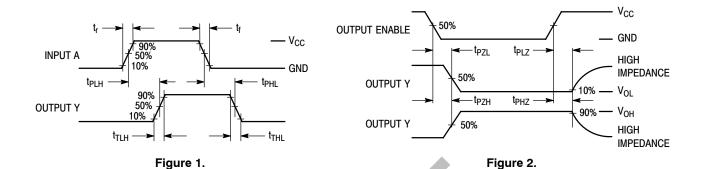
NOTES:

- 1. For propagation delays with loads other than 50 pF, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).
- 2. Information on typical parametric values can be found in Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

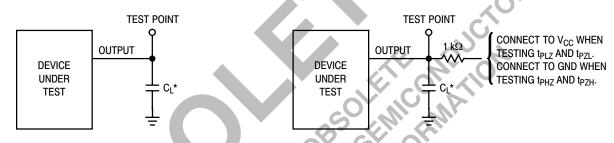
		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Buffer)*	60	pF

^{*} Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

SWITCHING WAVEFORMS



TEST CIRCUITS

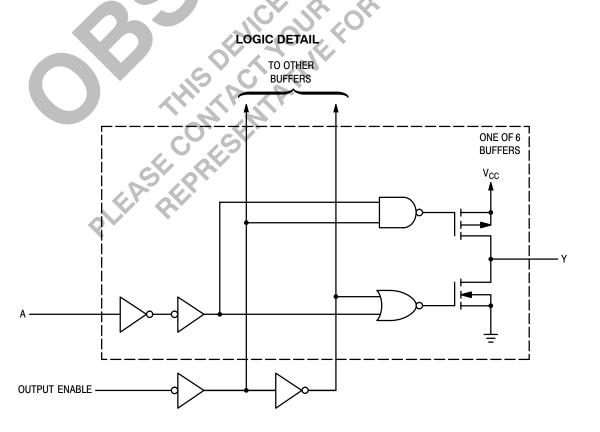


^{*}Includes all probe and jig capacitance

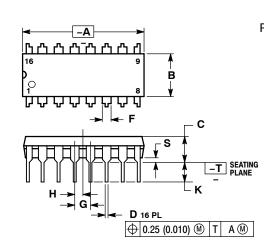
*Includes all probe and jig capacitance

Figure 3.

Figure 4.



OUTLINE DIMENSIONS

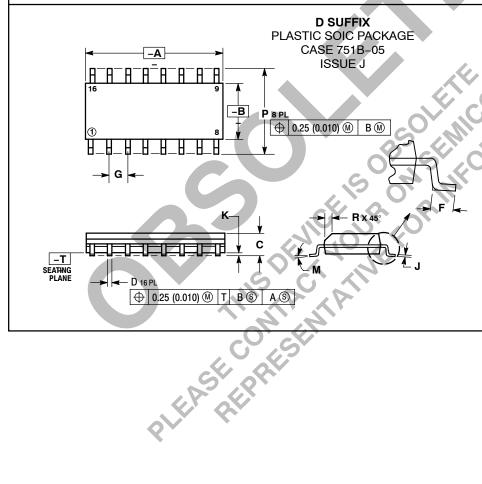


N SUFFIX PLASTIC PACKAGE CASE 648-08 **ISSUE R**

NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEADS WHEN
 FORMED PARALLEL.
 DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 ROUNDED CORNERS OPTIONAL.

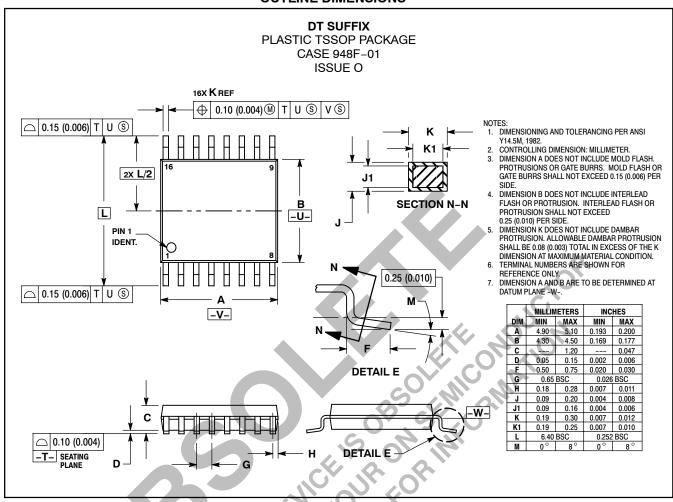
	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.070	1.02	1.77
G	0.	100 BSC	2	.54 BSC
Н	0.	050 BSC	1	.27 BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1 01



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION, ALLOWABLE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

OUTLINE DIMENSIONS



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